

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	IS&R	L1	3 (("4604150") or ("5736760") or ("5913132")). PN.	USPAT; US-PPGUB	2003/05/18 14:09			0
2	BRS	L2	0 WO-0115222-\$. did.	DERWENT	2003/05/18 14:16			0
3	IS&R	L3	0 ("WO-115222-\$. did. "). PN.	DERWENT	2003/05/18 14:11			0
4	BRS	L4	0 WO-0115222-\$. did.	DERWENT	2003/05/18 14:17			0
5	BRS	L5	0 WO-0115222-\$. DID.	DERWENT	2003/05/18 14:12			0
6	BRS	L6	0 DE-0002650-\$. did.	DERWENT	2003/05/18 14:17			0
7	BRS	L7	0 DE-00002650-\$. did.	DERWENT	2003/05/18 14:17			0
8	BRS	L8	0 WO-00115222-\$. did.	DERWENT	2003/05/18 14:17			0
9	BRS	L9	0 WO-0115222-\$. did.	DERWENT	2003/05/18 14:16			0
10	BRS	L10	0 WO-0115222-\$. did.	DERWENT	2003/05/18 14:17			0
11	BRS	L11	0 WO-00115222-\$. did.	DERWENT	2003/05/18 14:17			0
12	BRS	L12	0 DE-0002650-\$. did.	DERWENT	2003/05/18 14:17			0
13	BRS	L13	0 DE-00002650-\$. did.	DERWENT	2003/05/18 14:26			0
14	BRS	L14	3 infineon.asn. and steck.in. and schrems.in.	DERWENT	2003/05/18 14:27			0
15	BRS	L15	0 139256. URPN.	USPAT	2003/05/18 14:30			0
16	BRS	L16	0 19956078 . URPN .	USPAT	2003/05/18 14:32			0
17	BRS	FAMIL	1 2001-443143.NRAN .	DERWENT	2003/05/18 14:32			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
18	BRS	L18	0	20020137308.URPN.	USPAT	2003/05/18 14:33		0
19	BRS	FAMIL	Y	2001-202948.NRAN.	DERWENT	2003/05/18 14:33		0

DERWENT-ACC-NO: 2001-202948

DERWENT-WEEK: 200329

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TITLE: Forming a trench with a buried
trench plate comprises
non-doped silicon forming trench in substrate, forming
filling, removing oxide layer and doped silicate glass
oxide layer and glass filling and non-doped silicon
diffusing dopant

INVENTOR: HENNECKE, S; SCHREMS, M ; STECK, S

PATENT-ASSIGNEE: INFINEON TECHNOLOGIES AG[INFN] , SCHREMS
M[SCHRI], STECK
S[STECI]

PRIORITY-DATA: 1999DE-1039589 (August 20, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE		
LANGUAGE	PAGES	MAIN-IPC	
TW 493269 A		July 1, 2002	N/A
000	H01L 027/108		
WO 200115222 A1		March 1, 2001	G
022	H01L 021/8242		
DE 19939589 A1		May 10, 2001	N/A
000			
US 20020137308 A1		September 26, 2002	N/A
000	H01L 027/108		
		H01L 021/76	

DESIGNATED-STATES: JP KR US AT BE CH CY DE DK ES FI FR GB
GR IE IT LU MC NL PT
SE

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
TW 493269A	N/A	
2000TW-0116846	January 11, 2001	
WO 200115222A1	N/A	
2000WO-DE02650	August 3, 2000	
DE 19939589A1	N/A	
1999DE-1039589	August 20, 1999	
US20020137308A1	Cont of	
2000WO-DE02650	August 3, 2000	
US20020137308A1	N/A	
2002US-0078997	February 20, 2002	

INT-CL (IPC): H01L021/225, H01L021/76, H01L021/762,
 H01L021/8242,
 H01L027/108

ABSTRACTED-PUB-NO: US20020137308A

BASIC-ABSTRACT:

NOVELTY - Process comprises forming trench (1) in substrate (2); forming non-doped silicon oxide layer (4) on trench side walls; forming a doped silicate glass filling (3); removing the glass filling and the undoped silicon oxide layer from trench upper region; and diffusing dopant from filling through undoped silicon oxide layer and forming trench plate around trench lower region in the substrate.

DETAILED DESCRIPTION - Process for forming a trench with a buried trench plate comprises forming a trench (1) having upper and lower regions in a substrate (2); forming a non-doped silicon oxide layer (4) on the trench side walls in the upper and lower regions of the trench; forming a doped silicate glass filling (3) in the upper and lower regions; removing the glass filling and the non-doped silicon oxide layer from the upper region; and diffusing the dopant from the doped filling through the undoped silicon oxide

layer and forming a trench plate in the lower region of the trench in the substrate.

USE - In the production of integrated circuits containing capacitors.

ADVANTAGE - No dopant residues remain and current leakages are avoided.

DESCRIPTION OF DRAWING(S) - The drawing shows a cross-section through the trench structure.

Trench 1

Substrate 2

Silicate glass filling 3

Silicon oxide layer 4

ABSTRACTED-PUB-NO: WO 200115222A

EQUIVALENT-ABSTRACTS:

NOVELTY - Process comprises forming trench (1) in substrate (2); forming non-doped silicon oxide layer (4) on trench side walls; forming a doped silicate glass filling (3); removing the glass filling and the undoped silicon oxide layer from trench upper region; and diffusing dopant from filling through undoped silicon oxide layer and forming trench plate around trench lower region in the substrate.

DETAILED DESCRIPTION - Process for forming a trench with a buried trench plate comprises forming a trench (1) having upper and lower regions in a substrate (2); forming a non-doped silicon oxide layer (4) on the trench side walls in the upper and lower regions of the trench; forming a doped silicate glass filling (3) in the upper and lower regions; removing the

glass filling and the non-doped silicon oxide layer from the upper region; and diffusing the dopant from the doped filling through the undoped silicon oxide layer and forming a trench plate in the lower region of the trench in the substrate.

USE - In the production of integrated circuits containing capacitors.

ADVANTAGE - No dopant residues remain and current leakages are avoided.

DESCRIPTION OF DRAWING(S) - The drawing shows a cross-section through the trench structure.

Trench 1

Substrate 2

Silicate glass filling 3

Silicon oxide layer 4

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: FORMING TRENCH BURY TRENCH PLATE COMPRISE
FORMING TRENCH SUBSTRATE
 FORMING NON DOPE SILICON OXIDE LAYER DOPE
 SILICATE GLASS FILL
 REMOVE GLASS FILL NON DOPE SILICON OXIDE LAYER
 DIFFUSION DOPE

DERWENT-CLASS: L03 U11 U12 U13 U14

CPI-CODES: L04-C02; L04-C07E;

EPI-CODES: U11-C05G1B; U11-C07D4; U12-C02A1; U12-Q;
U13-C04B1A; U14-A03B4;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2001-060342

Non-CPI Secondary Accession Numbers: N2001-144779

DERWENT-ACC-NO: 2001-443143

DERWENT-WEEK: 200301

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TITLE: Production of an insulating collar
in a trench capacitor
comprises forming a trench in the
substrate, forming an insulating layer in the trench,
filling with filler material

INVENTOR: HAUPT, M; HENNECKE, S ; KOEHLER, D ; KRASEMANN, A
; SCHREML, M
; KOHLER, D ; SCHREMS, M ; STECK, S

PATENT-ASSIGNEE: INFINEON TECHNOLOGIES AG[SIEI] , HAUPT
M[HAUPI], KOHLER
D[KOHLI], KRASEMANN A[KRASI], SCHREMS M[SCHRI],
STECK S[STECI]

PRIORITY-DATA: 1999DE-1056078 (November 22, 1999)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC	
US 20020182819	A1	December 5, 2002		N/A
	000	H01L 021/20		
DE 19956078	A1	May 31, 2001		N/A
	011	H01L 021/8242		
WO 200139256	A2	May 31, 2001		G
	000			

H01L 021/00

DESIGNATED-STATES: US AT BE CH CY DE DK ES FI FR GB GR IE
IT LU MC NL PT SE TR

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO

APPL-DATE

US20020182819A1	Cont of
2000WO-DE04114	November 22, 2000
US20020182819A1	N/A
2002US-0153045	May 22, 2002
DE 19956078A1	N/A
1999DE-1056078	November 22, 1999
WO 200139256A2	N/A
2000WO-DE04114	November 22, 2000

INT-CL (IPC): H01L021/00, H01L021/20, H01L021/8242

ABSTRACTED-PUB-NO: DE 19956078A

BASIC-ABSTRACT:

NOVELTY - Production of an insulating collar in a trench capacitor comprises:

(a) preparing a semiconductor substrate (5), forming a trench (10) in the substrate;

(b) forming an insulating layer (35) in the trench to form an insulating collar (75);

(c) filling a lower region (50) of the trench with a sacrificial filler material (40) so that an upper region (45) of the trench remains free from the filler material;

(d) forming a structured layer on the insulating layer and on the filler material;

(e) forming an opening (60) in the structured layer, removing the filler material; and

(f) removing the insulating layer from the lower region by etching the insulating layer selectively to the structured layer.

DETAILED DESCRIPTION - Preferred Features: The structured layer and the filler

material are made of silicon nitride, polysilicon, amorphous silicon or photolacquer.

USE - Used in RAMs

ADVANTAGE - The collar is reliable.

DESCRIPTION OF DRAWING(S) - The drawing shows a section through the capacitor.

Substrate 5

Trench 10

Insulating layer 35

Filler material 40

Upper region 45

Lower region 50

Opening 60

CHOSEN-DRAWING: Dwg.1B/2

TITLE-TERMS: PRODUCE INSULATE COLLAR TRENCH CAPACITOR
COMPRIZE FORMING TRENCH

SUBSTRATE FORMING INSULATE LAYER TRENCH FILL
FILL MATERIAL

DERWENT-CLASS: L03 U11 U12 U13 U14

CPI-CODES: L03-G04A; L04-C12C; L04-C14A;

EPI-CODES: U11-C05B5; U11-C05G1B; U11-C07D4; U11-C08A3;
U12-C02A1; U12-Q;
U13-C04B1A; U14-A03B4;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2001-134190

Non-CPI Secondary Accession Numbers: N2001-327779